

2SC2406

Silicon NPN epitaxial planar type

For low-frequency and low-noise amplification

Complementary to 2SA1035

■ Features

- Low noise voltage NV
- High forward current transfer ratio h_{FE}
- Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	55	V
Collector-emitter voltage (Base open)	V_{CEO}	55	V
Emitter-base voltage (Collector open)	V_{EBO}	5	V
Collector current	I_C	50	mA
Peak collector current	I_{CP}	100	mA
Collector power dissipation	P_C	200	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Package

- Code
Mini3-G1
- Pin Name
 1. Base
 2. Emitter
 3. Collector

■ Marking Symbol: T

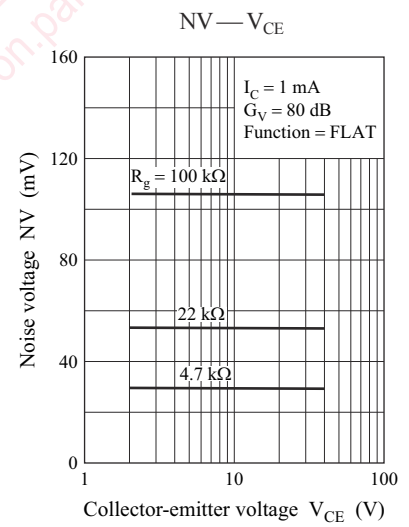
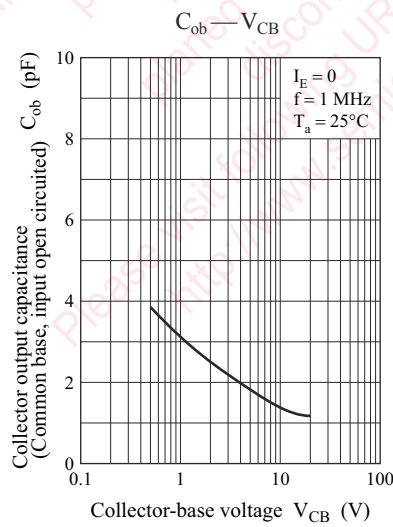
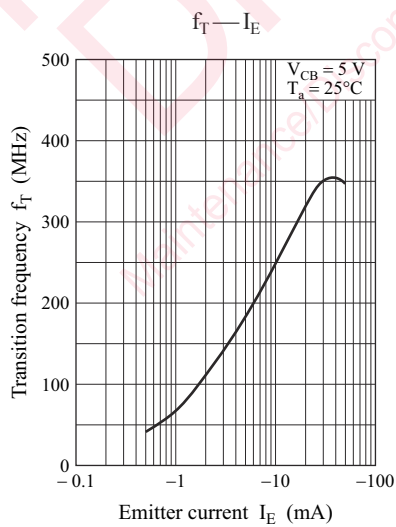
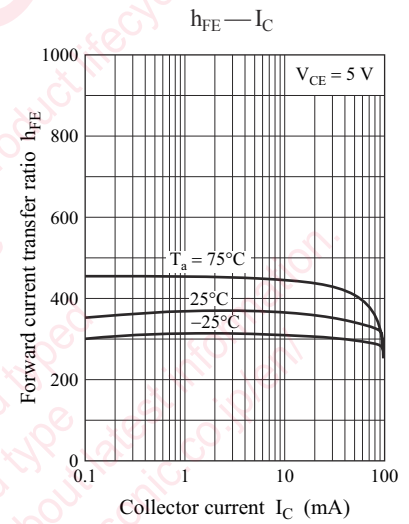
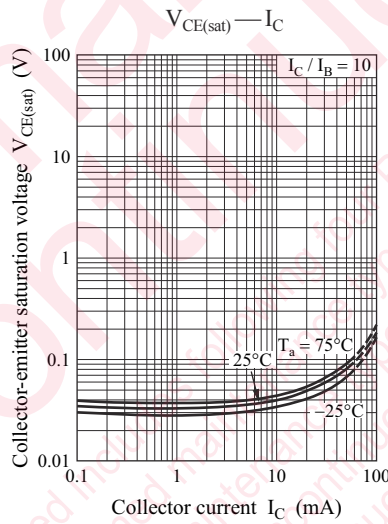
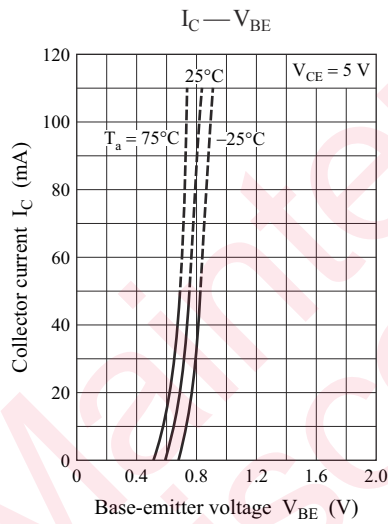
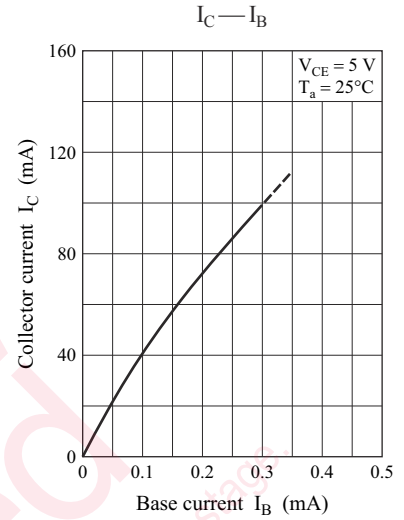
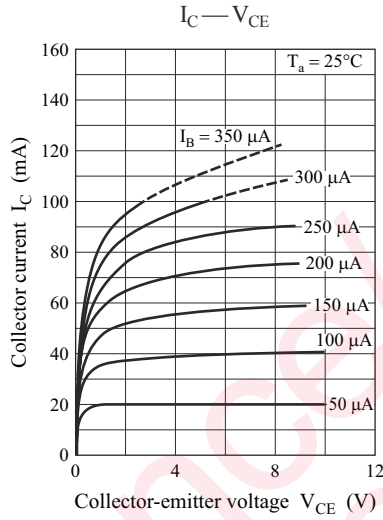
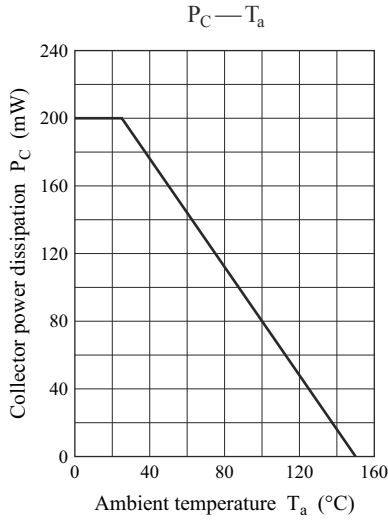
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

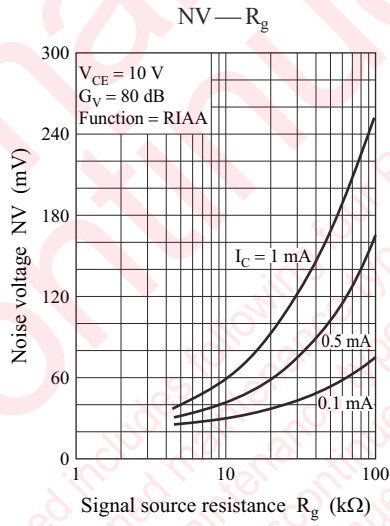
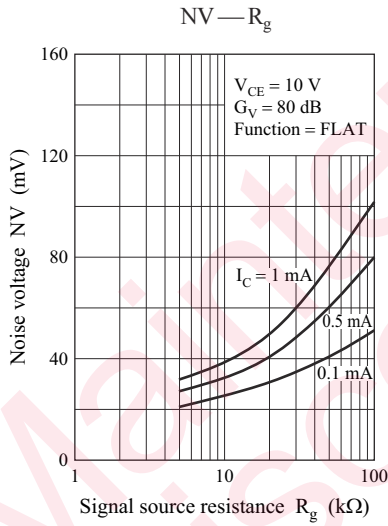
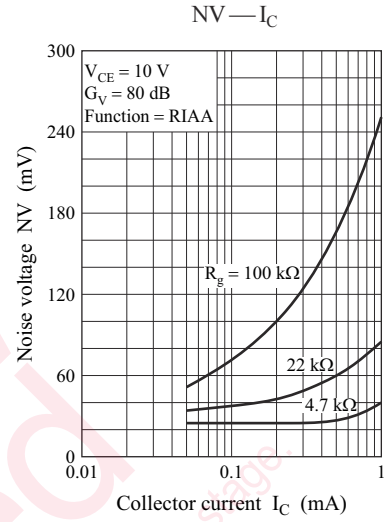
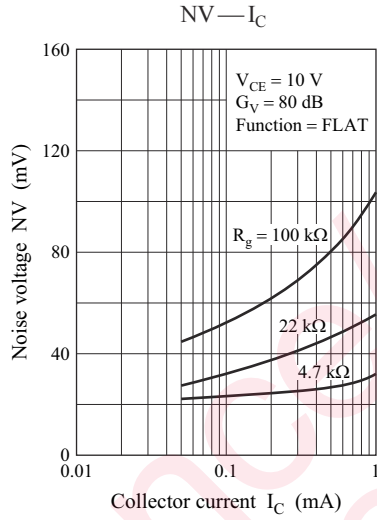
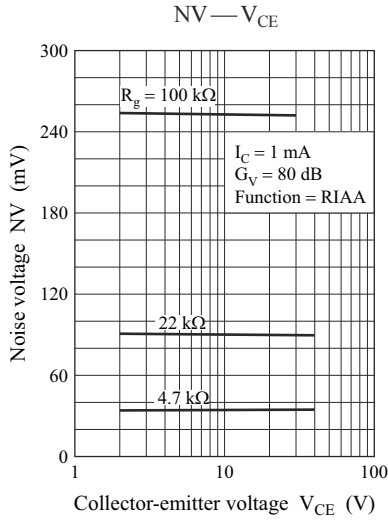
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = 10 \mu\text{A}, I_E = 0$	55			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = 2 \text{ mA}, I_B = 0$	55			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = 10 \mu\text{A}, I_C = 0$	5			V
Base-emitter voltage	V_{BE}	$V_{CE} = 1 \text{ V}, I_C = 100 \text{ mA}$		0.7	1.0	V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 10 \text{ V}, I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)	I_{CEO}	$V_{CB} = 10 \text{ V}, I_B = 0$			1	μA
Forward current transfer ratio *	h_{FE}	$V_{CE} = 5 \text{ V}, I_C = 2 \text{ mA}$	180		700	—
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 100 \text{ mA}, I_B = 10 \text{ mA}$			0.6	V
Transition frequency	f_T	$V_{CB} = 5 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Noise voltage	NV	$V_{CB} = 10 \text{ V}, I_C = 1 \text{ mA}, G_v = 80 \text{ dB}, R_g = 100 \text{ k}\Omega, \text{Function} = \text{FLAT}$		110		mV

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

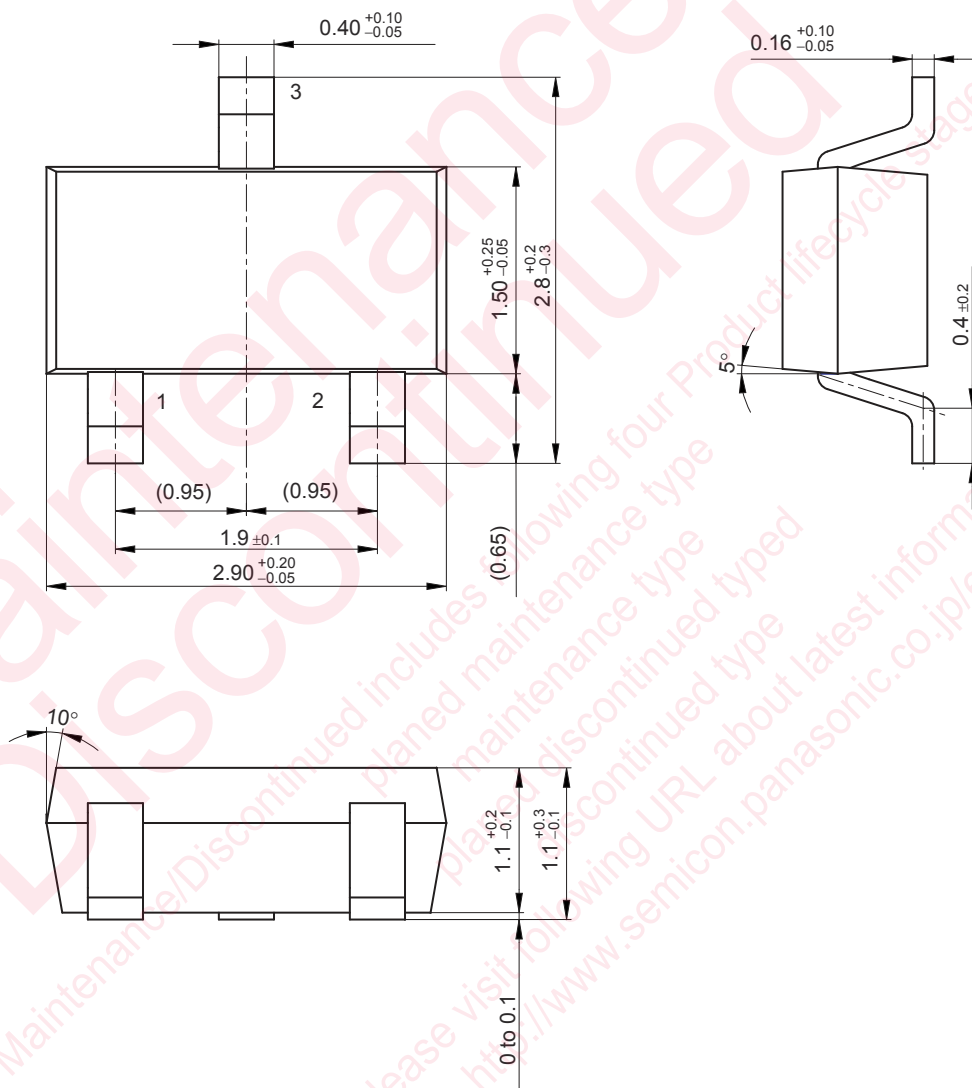
Rank	R	S	T
h_{FE}	180 to 360	260 to 520	360 to 700
Marking symbol	TR	TS	TT





Mini3-G1

Unit: mm



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